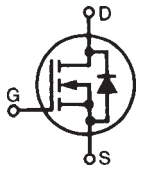
IXYS

Polar™ Power MOSFET HiPerFET™

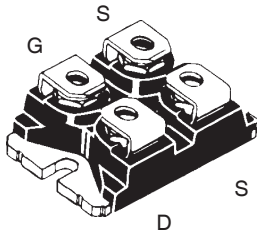
IXFN26N100P

V_{DSS} = 1000V
I_{D25} = 23A
$R_{DS(on)}$ ≤ 390mΩ
t_{rr} ≤ 300ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate D = Drain
S = Source

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		1000	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ		1000	V
V_{GSS}	Continuous		± 30	V
V_{GSM}	Transient		± 40	V
I_{D25}	T_C = 25°C		23	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}		65	A
I_{AR}	T_C = 25°C		13	A
E_{AS}	T_C = 25°C		1.0	J
dV/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$		20	V/ns
P_D	T_C = 25°C		595	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10s		300	°C
V_{ISOL}	50/60 Hz, RMS	t = 1min	2500	V~
	$I_{ISOL} \le$ 1mA	t = 1s	3000	V~
M_d	Mounting torque		1.5/13	Nm/lb.in.
	Terminal connection torque		1.3/11.5	Nm/lb.in.
Weight			30	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	1000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 1mA	3.5		6.5	V
I_{GSS}	V_{GS} = ± 30V, V_{DS} = 0V			± 200	nA
I_{DSS}	$V_{DS} = V_{DSS}$			25	μA
	V_{GS} = 0V, T_J = 125°C			2.0	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 13A, Note 1			390	mΩ

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

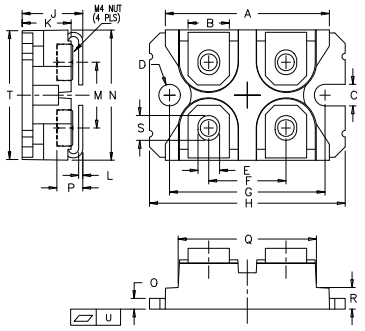
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Symbol	Test Conditions (T_J = 25°C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 13A, Note 1	13	22		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		11.9		nF
C_{oss}			690		pF
C_{rss}			60		pF
R_{Gi}	Gate input resistance		1.50		Ω
$t_{d(on)}$	**Resistive Switching Times**		45		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 13A		45		ns
$t_{d(off)}$	R_G = 1Ω (External)		72		ns
t_f			50		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 13A		197		nC
Q_{gs}			76		nC
Q_{gd}			85		nC
R_{thJC}				0.21	°C/W
R_{thCS}			0.05		°C/W

Source-Drain Diode (T_J = 25°C unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			26	A
I_{SM}	Repetitive, pulse width limited by T_{JM}			104	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 13A, -di/dt = 100A/μs			300	ns
Q_{RM}	V_R = 100V		1.2		μC
I_{RM}			12		A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

SOT-227B Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

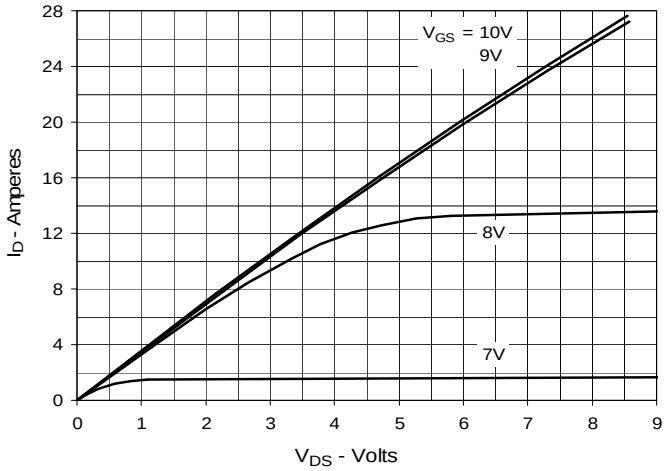


Fig. 2. Extended Output Characteristics @ 25ºC

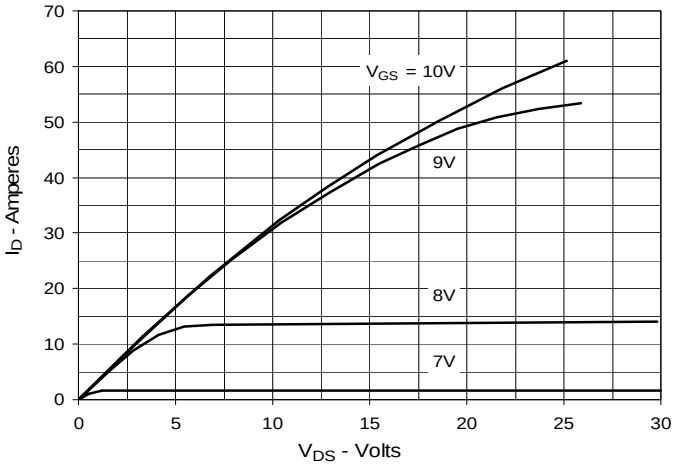


Fig. 3. Output Characteristics @ 125ºC

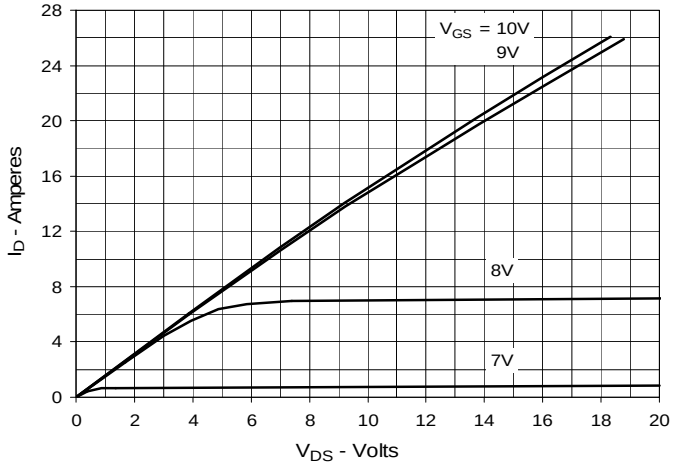


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 13A Value vs. Junction Temperature

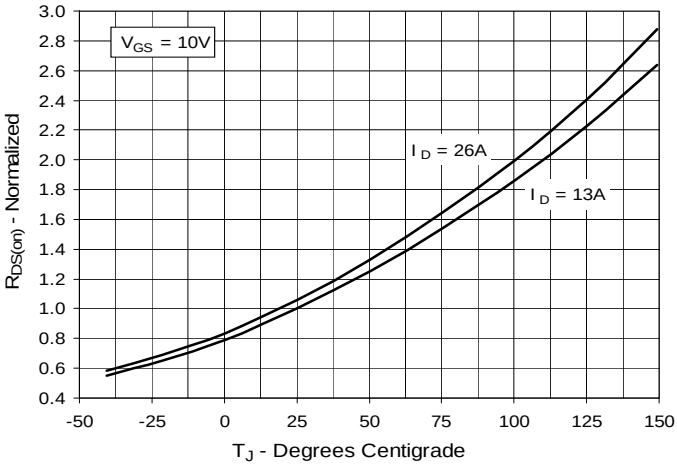


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 13A Value vs. Drain Current

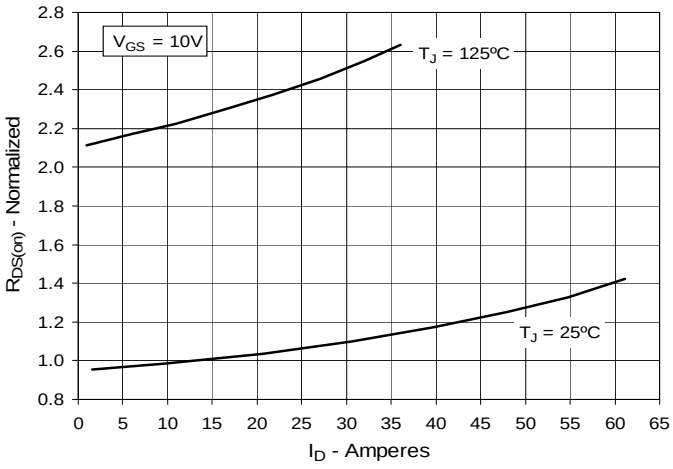
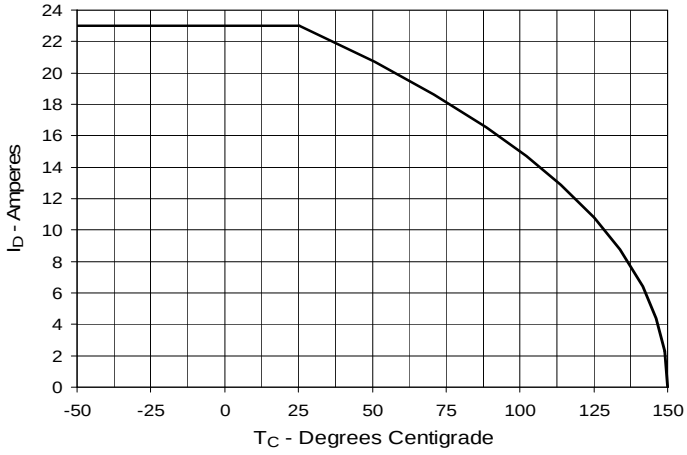


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

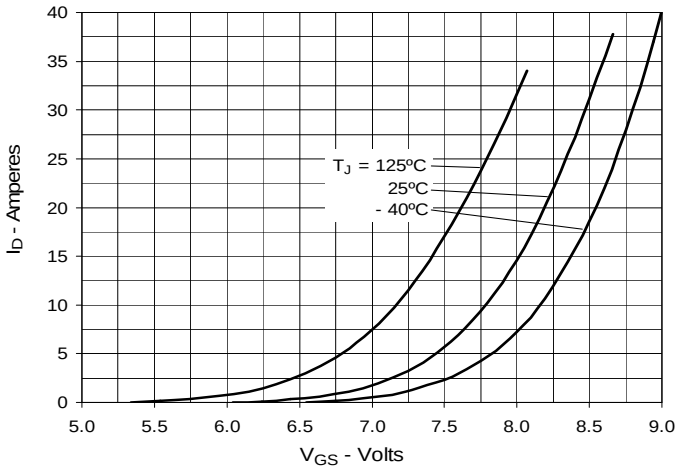


Fig. 8. Transconductance

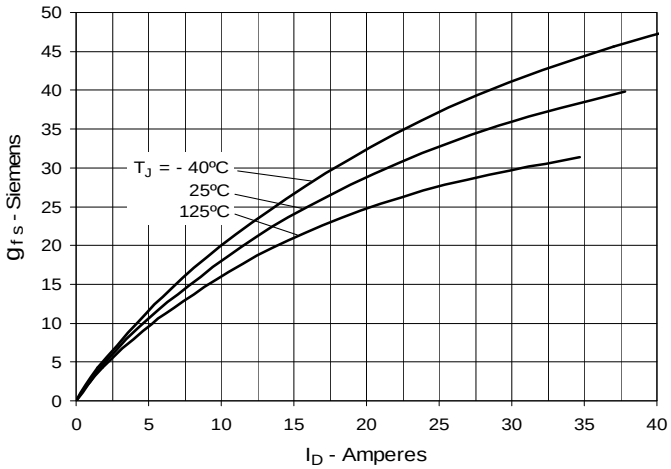


Fig. 9. Forward Voltage Drop of Intrinsic Diode

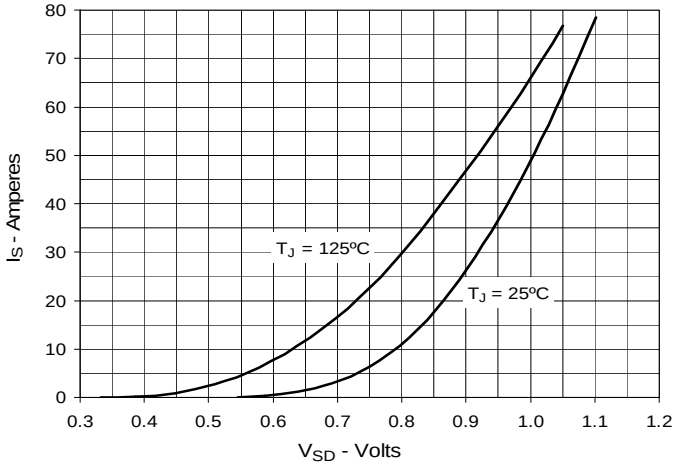


Fig. 10. Gate Charge

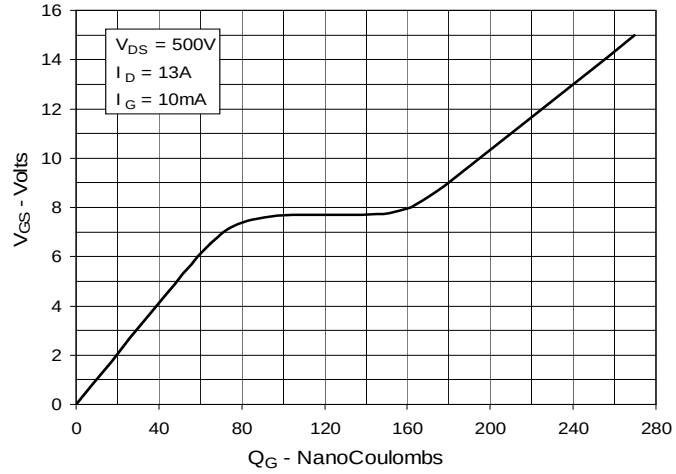


Fig. 11. Capacitance

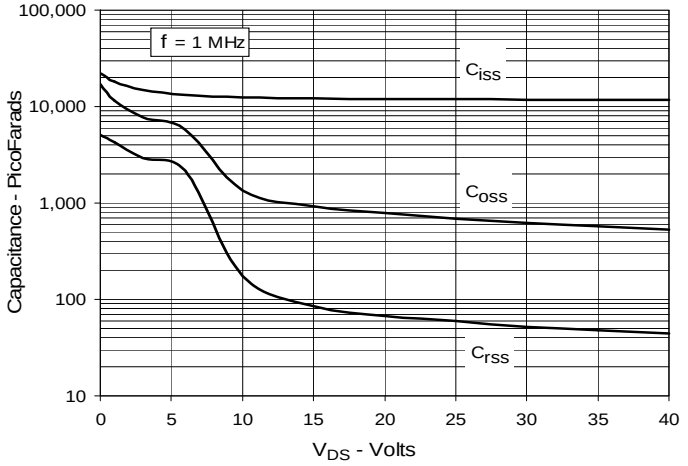
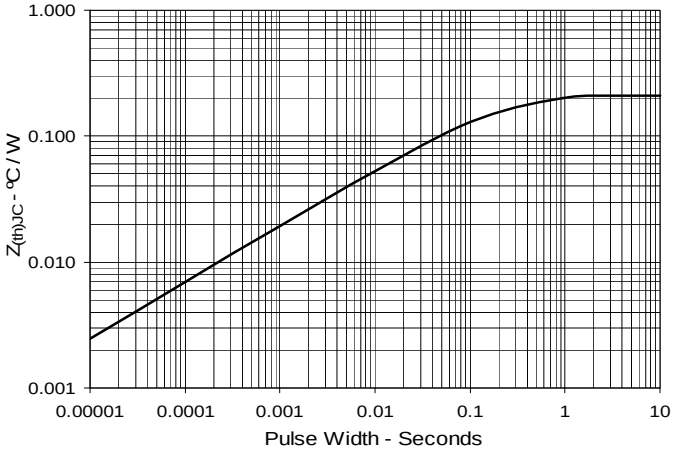


Fig. 12. Maximum Transient Thermal Impedance



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